TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1225

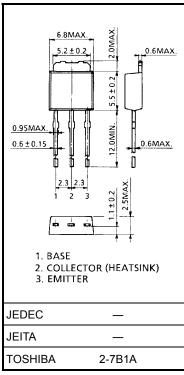
Power Amplifier Applications Driver Stage Amplifier Applications

- High transition frequency: fT = 100 MHz (typ.)
- Complementary to 2SC2983

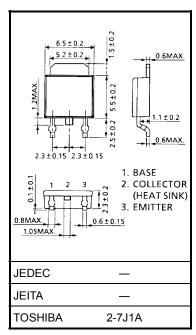
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	-160	V	
Collector-emitter voltage		V _{CEO}	-160	V	
Emitter-base voltage		V _{EBO}	-5	V	
Collector current		Ic	-1.5	Α	
Base current		ΙΒ	-0.3	Α	
Collector power dissipation	Ta = 25°C	Pc	1.0	W	
	Tc = 25°C	FC	15		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Unit: mm



Weight: 0.36 g (typ.)



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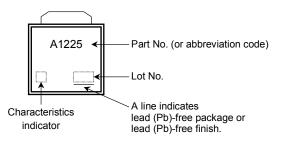


Electrical Characteristics (Ta = 25°C)

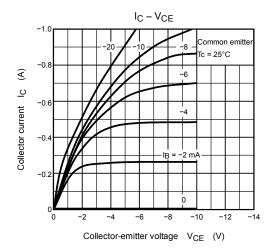
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = −160 V, I _E = 0	_	_	-1.0	μΑ
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$	_	_	-1.0	μA
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = -10 \text{ mA}, I_B = 0$	-160	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	I _E = -1 mA, I _C = 0	-5	_	_	V
DC current gain	h _{FE} (Note)	V _{CE} = -5 V, I _C = -100 mA	70	_	240	
Collector emitter saturation voltage	V _{CE (sat)}	I _C = -500 mA, I _B = -50 mA	_	_	-1.5	V
Base-emitter voltage	V _{BE}	V _{CE} = -5 V, I _C = -500 mA	_	_	-1.0	٧
Transition frequency	f _T	V _{CE} = -10 V, I _C = -100 mA	_	100	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = −10 V, I _E = 0, f = 1 MHz	_	30	_	pF

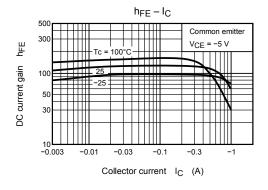
Note: hFE classification O: 70 to 140, Y: 120 to 240

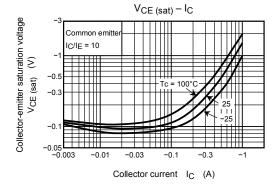
Marking

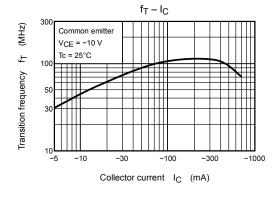


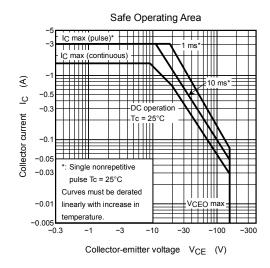
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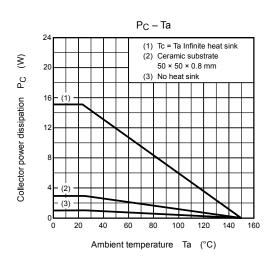












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